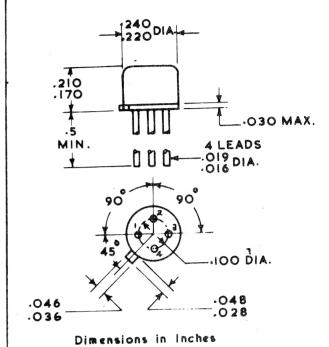
AMALGAMATED WIRELESS VALVE CO. PTY. LTD.

AS200 AS201



The AS200 and AS201 are n-p-n silicon planar epitaxial transistors for general use in H.F. and V.H.F. applications, having high f_T (900MHz) and typical R_{bb} , $C_{b'c}$ products of 8ps These units are in the TO-104 package.

DIMENSIONAL OUTLINE

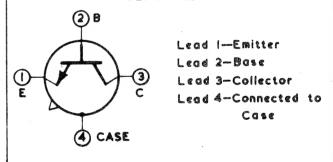


ABSOLUTE MAXIMUM RATINGS

Collector-base voltage = 45 volts Collector-emitter voltage = 45 volts (Base-emitter resistance = 100 K Ω)

Emitter-base voltage = 5 volts Emitter current = 50mA

TERMINAL DIAGRAM



THERMAL RATINGS

Dissipation in an ambient temperature up to $25\,^{\circ}\text{C}$ ---- $180\,\text{mW}$ max. Derate linearly to zero at $175\,^{\circ}\text{C}$.

During soldering lead temperature must not exceed 255°C for 10 secs. max. with 1/16" of can.

Storage temperature -65° C to 175° C

CHARACTERISTICS AT 25°C

AS200

AS201

PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNITS
V _{BE}	I _{BE} = 50mA			1.2	V
ICBO	V _{CB} = 1V			20	n A
I CBO	V _{CB} = 45V			1	μА
V _{EBF}	V _{CB} = 45V			1	V
V _{CER}	$I_C^- = 100 \mu A$, $R_{BE}^- = 100 KΩ$,	45	V
h _{fe}	$V_{CE} = 6V$, $I_{E} = 2mA$, $f = 100MHz$	7		14	
C _{b'c}	V _{CB} = 8V, I _E = 0		.55	.75	pF
-	AS200				
IB	$V_{CE} = 6V$, $I_{E} = 1mA$	3.6		13.8	μА
R _{bb'} C _{b'c}	$V_{CE} = 6V$, $I_{E} = 2mA$ $f = 31.9$	4		15	pS
	AS201				
I _B	$V_{CE} = 6V$, $I_{E} = 1mA$	6		37	μА
R _{bb'} C _{b'c}	$V_{CE} = 6V, I_{E} = 2mA, f = \frac{31.9}{MHz}$	4		10	pS
	With the Compliments of AMALGAMATED WIRELESS	VALVE	CO	PTV I	En
A	VICTORIA RD., RYDALMERE			638-	2411
				1	-

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